

REMARKS

The Applicants further traverse the restriction requirement imposed by the Examiner for the following reasons:

The Examiner contented that "the pre-claim chamber using a source RF power supply for supplying a source energy RF to the chamber, which is different than the method/process of pre-cleaning a wafer using a plasma in a chamber because the plasma is involved with reactant gases while the RF power deals with bias power and/or temperature only."

The Applicants respectfully submit that in the present invention, as clearly stated in the specification at Page 13, Paragraph 0028; Please see

"The wafer is then heated to an optimal temperature required for pre-cleaning of the wafer, and is then subjected to a reactive hydrogen or a ammonia plasma pre-cleaning process." Contrary to the Examiner's contention, the RF power is used to ignite a plasma in the chamber for the pre-cleaning of a wafer. The present invention method, as recited in independent method claim 9, which requires two essential steps of heating the wafer to a process temperature and pre-cleaning the wafer by plasma can therefore only be carried out in the present invention pre-

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clean chamber, as recited in independent apparatus Claim 1, which is equipped with a wafer heating apparatus and a source RF power supply. The restriction requirement imposed by the Examiner is therefore respectfully traversed.

The examination of the Group 2 Method Claims 9-20, together with the examination of the apparatus Claims 1-8 is respectfully requested of the Examiner.

Respectfully submitted,

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